¹⁸M. Fallot, J. Phys. Radium <u>5</u>, 153 (1944). ¹⁹C. P. Bean and D. S. Rodbell, Phys. Rev. <u>126</u>, 105 (1962).

²⁰R. C. Wayne, Phys. Rev. <u>170</u>, 523 (1968).

²¹D. L. Williamson, S. Bukshpan, R. Ingalls, and H. Shechter, to be published.

²²C. E. Johnson, M. S. Ridout, and T. E. Cranshaw,

Proc. Phys. Soc., London 81, 1079 (1963); Y. Naka-

mura, M. Shiga, and N. Shikazono, J. Phys. Soc. Jap. <u>19</u>, 1177 (1964).

²³J. M. Leger and C. Susse-Loriers, Phys. Lett. <u>37A</u>, 145 (1971).

 24 L. Kaufman and M. Cohen, Trans. AIME 206, 1393 (1956).

²⁵J. R. Patel and M. Cohen, Acta Met. <u>1</u>, 531 (1953).

²⁶D. G. Howard, B. D. Dunlap, and J. G. Dash, Phys. Rev. Lett. <u>15</u>, 628 (1965).

²⁷O. A. Khomenko, Fiz. Metal. Metalloved. <u>26</u>, 269 (1968) [Phys. Metals Metallogr. (USSR) <u>26</u> (2), 84 (1968)].

²⁸D. R. Rhiger and R. Ingalls, Bull. Amer. Phys. Soc. <u>16</u>, 849 (1971); the value of dT_N/dP should be replaced by the value in the present Letter.

²⁹D. Rhiger, R. Ingalls, and D. L. Williamson, Bull. Amer. Phys. Soc. 15, 1360 (1970).

³⁰D. I. Bower, E. Claridge, and I. S. T. Tsong, Phys. Status Solidi 29, 617 (1968).

³¹S. Margulies and J. R. Ehrman, Nucl. Instrum. Methods <u>12</u>, 131 (1961).

³²C. M. Fowler, F. S. Minshall, and E. G. Zukas, in Response of Metals to High Velocity Deformation,

edited by P. G. Shewman and V. F. Zakay (Interscience, New York, 1961), p. 275.

³³D. L. Williamson, S. Bukshpan, and R. Ingalls, to be published.

³⁴L. D. Blackburn, L. Kaufman, and M. Cohen, Acta Met. <u>13</u>, 533 (1965).

 35 L. E. Millet and D. L. Decker, Phys. Lett. <u>29A</u>, 7 (1969).

³⁶M. Shiga, Phys. Status Solidi (b) <u>43</u>, K37 (1971).

³⁷In magnetically inhomogenous Fe-Ni a field of 31 kOe is reported for the antiferromagnetic regions

[H. Asano, J. Phys. Soc. Jap. 27, 542 (1969)].

³⁸D. R. Rhiger, to be published.

³⁹T. F. Smith, J. A. Mydosh, and E. P. Wohlfarth, Phys. Rev. Lett. <u>27</u>, 1732 (1971).

Identification of a Class of Disordered One-Dimensional Conductors

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We find that over thirty solids having high one-dimensional conductivity form a class of materials whose electronic properties are determined principally by structural disorder.

Recently, considerable experimental work¹⁻⁷ has been reported on a number of highly conducting solids in which the propagation of electrons is confined effectively to one dimension. The most prominent examples are some of the "mixedvalence" complexes⁸ of platinum and iridium, and certain salts of the organic ion-radical tetracyanoquinodimethan (TCNQ).⁹ Here we recognize the central significance, for the electronic properties of these materials, of a fact which has been overlooked in previous interpretations: X-ray crystallographic data, where available,^{8,11,12} show them to be structurally disordered. Indeed, this is to be expected on chemical grounds¹⁰ for the entire class. Exact theorems have been proven¹³ stating that all electronic states in any disordered one-dimensional structure are localized.

The existence of such a class of materials thus acquires special significance.

Electronic conductivity in disordered one-dimensional systems can occur only by phononassisted hopping,¹⁴ and we find that the available data are understood on this basis. Moreover, we find that the magnetic susceptibility, the optical properties, and the ac conductivity all consistently support the same point of view. Our work resolves certain difficulties in the treatment by Epstein *et al.*⁴ of the *N*-methyl-phenazinium salt NMP-TCNQ as a realization of the onedimensional Mott-Hubbard model, and in the interpretation by Kuse and Zeller⁷ and others⁵⁻⁸ of K₂Pt(CN)₄Br_{0.3}·2.3H₂O as a one-dimensional metal.

It will be convenient for our purposes to divide

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these materials into three groups. By I we shall mean any of the twenty or so known "mixedvalence" square-planar complex platinum salts of which the most widely studied example is $K_2Pt(CN)_4Br_{0.3}$ · 2.3H₂O (we shall refer to this prototype specifically as Ia). Among the organic systems, we single out as II the simple⁹ NMP-TCNQ salt studied extensively by Epstein et al.,⁴ and refer to the highly conducting complex⁹ TCNQ salts collectively as III. Specific examples are quinolinium TCNQ, (IIIa) and acridinium TCNQ, (IIIb). The crystal structures of all three groups are gualitatively similar in that they all contain arrays of infinite, parallel, periodic chains of stacked planar anions. In I, the interchain channels are found⁸ to contain a random array of ions, and we infer that they exert on the conduction electrons a potential which varies randomly along the chains. The situation is somewhat different in II and III, where all lattice sites are occupied, but the organic cations are asymmetric, and can occupy their lattice sites in either of two inequivalent orientations. X-ray studies^{11,12} suggest that the distribution of orientations is random, presumably with effects similar to those in I. This form of disorder could be eliminated by preparing a form of II or III with a symmetric cation, but attempts to do so⁹ have led to drops of several orders of magnitude in the conductivity¹⁵ and to crystal structures¹⁶ resembling those expected from the well-known Peierls distortion¹⁷ of a one-dimensional electron gas. These observations are consistent with the fact that the logarithmic divergence in the dielectric constant which gives rise to the Peierls distortion occurs only for an ordered array.

In general the wave functions in a weakly disordered material are extended over several lattice sites. Accordingly, we assign to each wave function ψ_i (of energy E_i near the Fermi energy) centered on the site *i*, a length *L*. We denote by α the rate of decay of the wave function at its edges, and ignore the energy dependences of α , *L*, and the density of states ρ_0 . The probability Γ_{ij} of hopping between two states *i* and *j* depends upon, among other things, the overlap of the wave functions and thus on αR_{ij} , where R_{ij} is some length which depends on the detailed structure of the wave function and the distance $|x_i - x_j|$. Following Mott¹⁸ and Ambegoakar, Halperin, and Langer,¹⁹ (AHL) we have that

$$\Gamma_{ij} \simeq \gamma_0 \exp(-2\alpha R_{ij} - E_{ij}/kT), \quad R_{ij} > L$$

$$\simeq \gamma_0 \exp(-E_{ij}/kT), \quad R_{ij} < L, \qquad (1)$$

where γ_0 is of the order of a typical phonon frequency and $E_{ij} \simeq |E_i| + |E_j| + |E_i - E_j|$ if the energies E_i and of the eigenstates are much greater than kT. Since L is larger than the lattice constant a, our band consists of a dense set of strongly overlapping states; the theories of Mott and AHL, which start from a condition of strong localization, must therefore be applied with care. However, the temperature dependence of the conductivity follows from purely dimensional arguments; and we believe that our introduction of R_{ij} , which is not in general equal to $|x_i - x_j|$, contains the correct physics for the present problem. The Mott and AHL theories applied to one dimension predict for the conductivity

$$\ln \sigma \sim - (T_0/T)^{1/2},$$
 (2)

where $T_0 = \alpha \nu_c / k \rho_0$, with ν_c a dimensionless constant representing the number of states in a region of length $2R_{\text{max}} = \alpha^{-1} (T_0/T)^{1/2}$ having energies within $E_{\text{max}} = \frac{1}{2} k (TT_0)^{1/2}$ of the Fermi level.

In Fig. 1 we have replotted as log σ versus $T^{-1/2}$ some of the published conductivity data for I, II,



FIG. 1. Conductivity σ of I (Ref. 7), II (Ref. 1), IIIa (Ref. 3), and IIIb (Ref. 3) replotted versus $T^{-1/2}$. For I and II, σ is in Ω^{-1} cm⁻¹. For IIIa and IIIb, σ_{290} is the conductivity at 290 K.

and III. The agreement with theory is particularly impressive for IIIa and Ia, where it persists over twelve orders of magnitude in the conductivity. We suspect that the departures at the lowest temperatures are manifestations of interchain tunneling: As $R_{\rm max}$ becomes much larger than the distance between chains, tunneling must eventually become insensitive to the anisotropy of the crystal, and the three-dimensional $T^{-1/4}$ law^{18,19} should hold. More extensive low-temperature studies are needed to test this conjecture, but it is clear that the present data suggest such behavior, particularly in IIIb.

The departures at high temperatures, on the other hand, are to be expected from our onedimensional model, and can in fact be used to estimate αL and ν_c as follows. Our analysis up to this point can hold only for large R_{\max} : It must break down when R_{\max} becomes so short that no Γ_{ij} which contributes to the conductivity depends strongly on R_{ij} . From (1) this is true above a temperature T_H such that

$$R_{\max}(T_H) = \frac{1}{2} \alpha^{-1} (T_0/T_H)^{1/2} = L, \qquad (3)$$

whence

$$T_{H} = T_{0} / 4 \alpha^{2} L^{2}. \tag{4}$$

For $T > T_H$ there are at least ν_c states within the energy interval $2E_{\max}(T_H)$ which overlap the initial state *i* strongly. The activation energy is then of the order of the average energy separation between these states:

$$\ln\sigma \sim \frac{-k(T_0T_H)^{1/2}}{kT\nu_c} = -(2\alpha L\nu_c)^{-1}\frac{T_0}{T}, \quad T > T_H.$$
(5)

Such behavior can persist with increasing temperature only until kT is of the order of the activation energy. This will of course occur at a temperature T_D defined by

$$T_{\rm p} = T_{\rm o}/2\alpha L \nu_c \,. \tag{6}$$

Above T_D , the conduction must be essentially diffusive, with a conductivity given by the Ein-

stein equation in the limit $T \gg T_D$:

$$\sigma = (Nne^2/kT) \langle \gamma_0 \rangle \langle (x_i - x_j)^2 \rangle.$$
⁽⁷⁾

Here N is the number of chains per unit crosssectional area and n is the electron density on the chains. If at these temperatures $\langle (x_i - x_j)^2 \rangle$ is of order a^2 , and if $\langle \gamma_0 \rangle \simeq 10^{12} \text{ sec}^{-1}$, the conductivity calculated from (7) agrees well with the experimental values¹⁻⁷ of ca. $1-3 \times 10^2 \ \Omega^{-1}$ cm⁻¹ measured at room temperature for I, II, and III. We note that we are not dealing here with a transition to the metallic state as usually defined: The mean free path λ calculated from the one-dimensional nearly free-electron formula $\sigma = 2Ne^2/\pi\hbar$ is of order *a*. Under this condition there can be no long-range phase coherence, and the conduction process is described more appropriately interms of Brownian motion than of wave propagation.

It is difficult to measure T_D , but if we identify it as the temperature at which the conductivity passes through a maximum, we can combine (5) and (7) to determine

$$\nu_c^2 \simeq T_0 T_D / T_H^2. \tag{8}$$

Since ν_c depends only upon the dimensionality of the system, the ratio (8) should be a constant of the entire class of materials: Its invariance then represents a test of the crude theory presented here. We have applied (4) and (8) to the data of Fig. 1 to compute αL and ν_c for II, IIIa, and IIIb; ν_c cannot be determined for Ia because T_D is presumably higher than the temperature at which the compound decomposes. The results are listed in Table I. We consider the agreement among the computed values of ν_c excellent in view of the approximations involved and the difficulty in reading the data from the published graphs.

From their thorough experimental study of II, Epstein *et al.*⁴ have interpreted this system, with its half-filled band, as a realization of the simple (ordered) one-dimensional Hubbard model, and

TABLE I. Values of αL and ν_c calculated using (4) and (8) and T_0 , T_H , and T_D obtained from data and references of Fig. 1.

$T_H T_D$ (K) (K) αL	ν _c
20 580 ^a 11.0	•••
50 200 0.3	4.6
30 230 3.5	4.0
70 130 4.4	4.8
	$\begin{array}{c ccccc} \Gamma_{H} & T_{D} \\ \hline K & (K) & \alpha L \\ \hline 20 & 580 & 11.0 \\ 50 & 200 & 0.3 \\ 30 & 230 & 3.5 \\ 70 & 130 & 4.4 \end{array}$

^aEstimated assuming $\nu_c = 4.5$.

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have asserted that a Mott-Hubbard transition from semiconductor to metal occurs with increasing temperature. The apparent temperature dependence of the activation energy for conductivity would then be due to an (as yet uncalculated) continuous renormalization of the Hubbard gap as the temperature is raised. This explanation does not appear to be consistent with several experimental facts. First, at 10 K the ac conductivity of II at 10¹⁰ Hz is known² to be 4 orders of magnitude larger than the dc; we do not believe that this can be reconciled with the Hubbard gap of 0.17 eV demanded by the experiments of Epstein *et al.*⁴ On the other hand, this behavior, as well as the temperature dependence of the ac conductivity and dielectric constant,² is precisely what is expected²⁰ if II is disordered. Strikingly similar results have been obtained for Ia⁶ and IIIb.² Unfortunately the ac measurements have been made at only two frequencies, so that a detailed comparison with theory is not possible. Second, x-ray measurements¹¹ have shown explicitly that II is disordered, and the fit by the $T^{-1/2}$ law for the dc conductivity persuades us that the Mott-Hubbard transition need not be invoked for II.

That is not to say that electron correlations are totally unimportant to the properties of these materials. The temperature dependence of the magnetic susceptibility of II as well as of I and III can be understood in terms of disorder if there is a repulsion energy between opposite spins in the same localized state. As Mott²¹ has emphasized, this will give rise to a fraction of states with unpaired spins and to a susceptibility which includes the sum of a Curie-Weiss term $\chi_c(T)$ and a temperature-independent term χ_{p} . The measured spin susceptibilities of Ia,²² II,^{1,4} and IIIa²³ are of approximately this form. In II,^{1,4} the crossing point at which $\chi_c(T) \simeq \chi_p$ occurs at a temperature T_{M} similar to T_{D} , the temperature of maximum conductivity; Epstein et al.4 have interpreted this as a manifestation of a Mott-Hubbard transition. In I²² and in IIIa,²³ however, T_{M} is quite different from T_{D} , and in this context it becomes clear that the rough agreement in ${\rm I\!I}$ is probably a coincidence: T_M is primarily a measure of the correlation energy and T_p of the density of states and the degree of disorder.

Note added in proof.-After completion of this

work, we have learned that Professor N. F. Mott and Professor W. A. Little have come to some of the same conclusions reported in this paper.

Two of us (A.N.B. and R.B.W.) are grateful to Professor J. H. Perlstein for originally bringing these compounds to our attention. One of us (C.M.V.) acknowledges a useful discussion with Dr. W. F. Brinkman.

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¹I. F. Shchegolev et al., Zh. Eksp. Teor. Fiz., Pis'ma Red. 8, 353 (1968) [JETP Lett. 8, 218 (1968)].

²L. I. Buravov et al. Pis'ma Zh. Eksp. Teor. Fiz. 12, 142 (1970) [JETP Lett. 12, 99 (1970)].

³L. I. Buravov, D. N. Fedutin, and I. F. Shchegolev, Zh. Eksp. Teor. Fiz. 59, 1125 (1971) [Sov. Phys. JETP 32, 612 (1971)]. ⁴A. J. Epstein, S. Etemad, A. F. Garito, and A. J.

Heeger, Solid State Commun. 9, 1803 (1971).

⁵M. J. Minot and J. H. Perlstein, Phys. Rev. Lett. 26, 371 (1971).

⁶A. S. Bernblyum et al., Pis'ma Zh. Eksp. Teor. Fiz. 13, 619 (1971) [JETP Lett. 13, 440 (1971)].

⁷D. Kuse and H. R. Zeller, Phys. Rev. Lett. 27, 1060 (1971).

⁸K. Krogmann, Angew. Chem. Int. Ed. Engl. 8, 35 (1969), and references contained therein.

⁹L. R. Melby, Can. J. Chem. 43 1448 (1965).

¹⁰R. B. Weisman and A. N. Bloch, to be published.

¹¹C. J. Fritchie, Acta Crystallogr. <u>20</u>, 892 (1966).

¹²H. Kobayashi, F. Marumo, and Y. Saito, Acta

Crystallogr., Sect. B 27, 373 (1971).

¹³R. E. Borland, Proc. Phys. Soc., London 78, 926 (1961). This was anticipated on physical grounds by N. F. Mott and W. D. Twose, Advan. Phys. 10, 107 (1961).

¹⁴See for example, N. F. Mott, Advan. Phys. <u>16</u>, 49 (1967).

 $^{15}\mbox{One}$ of us (A.N.B.) is grateful to Z. Soos for pointing this out to him.

¹⁶For example, C. J. Fritchie and P. Arthur, Acta Crystallogr. 21, 139 (1966).

¹⁷R. E. Peierls, Quantum Theory of Solids (Oxford Univ. Press, London, 1955), p. 108 ff.

¹⁸N. F. Mott, Phil. Mag. 19, 835 (1969).

¹⁹V. Ambegaokar, B. I. Halperin, and S. J. Langer, Phys. Rev. B 4, 2612 (1971).

²⁰M. Pollak and T. H. Geballe, Phys. Rev. 122, 1742 (1961).

²¹N. F. Mott, Phil. Mag. 25, 935 (1971).

²²F. J. Di Salvo and M. Butler, to be published.

²³R. G. Kepler, J. Chem. Phys. <u>39</u>, 3528 (1963).